



Product Overview

EMH2801: P-Channel Power MOSFET, -20V, -3A, 85mΩ, Single EMH8 with Schottky Diode

For complete documentation, see the data sheet

Product Description

EMH2801 is a P-Channel Power MOSFET, -20V, -3A, 85mΩ, Single EMH8 with Schottky Diode for General-Purpose Switching Device Applications.

Features

- Composite type with a P-Channel Silicon MOSFET and a Schottky Barrier Diode contained in one package facilitating high-density mounting
- MOSFET : Low ON-resistance
- MOSFET : 1.8V drive
- SBD : Small switching noise
- SBD : Low forward voltage (IF = 2.0A, VF max = 0.46V)
- Halogen free compliance

Part Electrical Specifications

Product	Compliance	Status	Channel Polarity	Configuration	V _{DS} (BR) Min (V)	V _{GS} Max (V)	V _{GS} (th) Max (V)	I _D Max (A)	P _D Max (W)	r _{DS(on)} Max @ V _{GS} = 2.5 V (m)	r _{DS(on)} Max @ V _{GS} = 4.5 V (m)	r _{DS(on)} Max @ V _{GS} = 10 V (m)	Q _g Typ @ V _{GS} = 4.5 V (nC)	Q _g Typ @ V _{GS} = 10 V (nC)	Q _{gd} Typ @ V _{GS} = 4.5 V (nC)	Q _{tr} Typ (nC)	C _{iss} Typ (pF)	C _{oss} Typ (pF)	C _{rss} Typ (pF)	Packaging Type
EMH2801-TL-H	Pb-free Halide free	Active	P-Channel	with Schottky Diode	-20	10	-1.3	-3	1	137	85		4		1.1		320	66	50	SO-T-383 FL / EMH-8

For more information please contact your local sales support at www.onsemi.com

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